



STX13003

HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

- ST13003 SILICON IN TO-92 PACKAGE
- MEDIUM VOLTAGE CAPABILITY
- LOW SPREAD OF DYNAMIC PARAMETERS
- MINIMUM LOT-TO-LOT SPREAD FOR RELIABLE OPERATION
- VERY HIGH SWITCHING SPEED

APPLICATIONS:

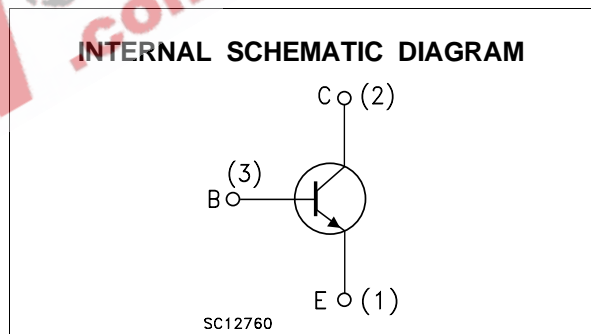
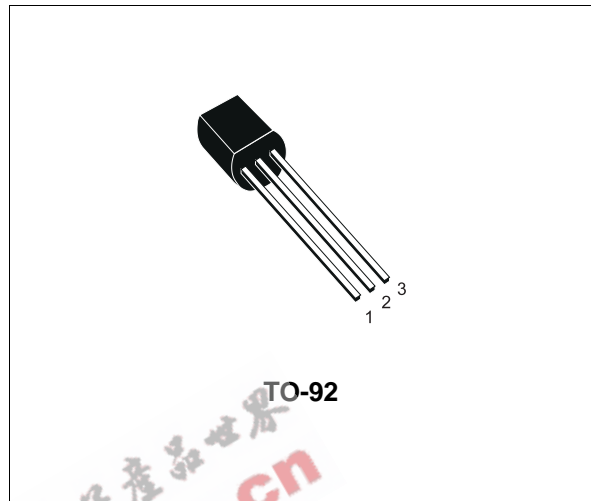
- ELECTRONIC BALLASTS FOR FLUORESCENT LIGHTING

DESCRIPTION

The device is manufactured using high voltage Multi Epitaxial Planar technology for high switching speeds and medium voltage capability.

It uses a Cellular Emitter structure with planar edge termination to enhance switching speeds while maintaining the wide RBSOA.

The STX13003 is designed for use in compact fluorescent lamp application.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CES}	Collector-Emitter Voltage ($V_{BE} = 0$)	700	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	400	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0, I_B = 0.5 \text{ A}, t_p < 10 \mu\text{s}, T_j < 150^\circ\text{C}$)	$V_{(BR)EBO}$	V
I_C	Collector Current	1	A
I_{CM}	Collector Peak Current ($t_p < 5 \text{ ms}$)	3	A
I_B	Base Current	0.5	A
I_{BM}	Base Peak Current ($t_p < 5 \text{ ms}$)	1.5	A
P_{tot}	Total Dissipation at $T_C = 25^\circ\text{C}$	1.5	W
T_{stg}	Storage Temperature	-65 to 150	$^\circ\text{C}$
T_j	Max. Operating Junction Temperature	150	$^\circ\text{C}$

STX13003

THERMAL DATA

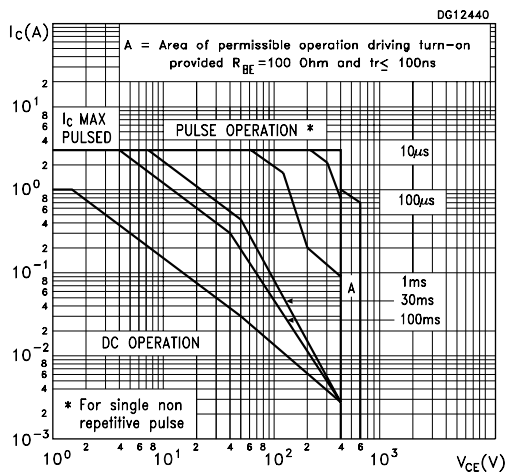
R _{thj-case}	Thermal Resistance Junction-case	Max	83.3	°C/W
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ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

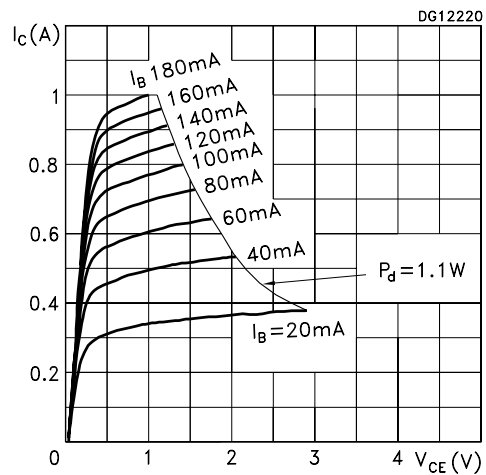
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
I _{CEV}	Collector Cut-off Current (V _{BE} = -1.5V)	V _{CE} = 700V V _{CE} = 700V T _j = 125°C			1 5	mA mA	
V _{(BR)EBO}	Emitter-Base Breakdown Voltage (I _C = 0)	I _E = 10 mA	9		18	V	
V _{CEO(sus)*}	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 10 mA L = 25 mH	400			V	
V _{CE(sat)*}	Collector-Emitter Saturation Voltage	I _C = 0.5 A I _C = 1 A I _C = 1.5 A			0.5 1 3	V V V	
V _{BE(sat)*}	Base-Emitter Saturation Voltage	I _C = 0.5 A I _C = 1 A			1 1.2	V V	
h _{FE*}	DC Current Gain	I _C = 0.5 A I _C = 1 A			8 5	35 25	
t _r t _s t _f	RESISTIVE LOAD Rise Time Storage Time Fall Time	I _C = 1 A I _{B1} = 0.2 A T _p = 25 μs			1 4 0.7	μs μs μs	
t _s	INDUCTIVE LOAD Storage Time	I _C = 1 A V _{BE} = -5 V V _{clamp} = 300 V		0.8		μs	

* Pulsed: Pulse duration = 300μs, duty cycle = 1.5 %.

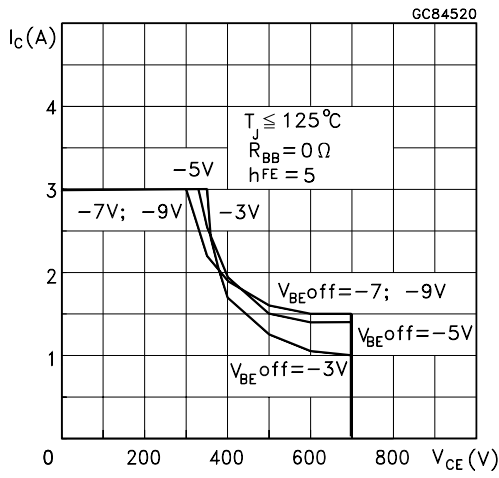
Safe Operating Area



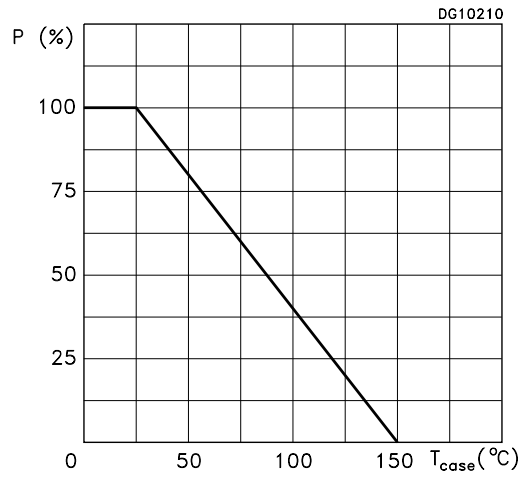
Output Characteristics



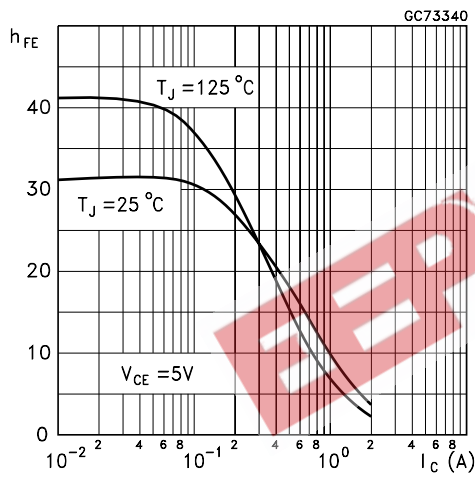
Reverse Biased SOA



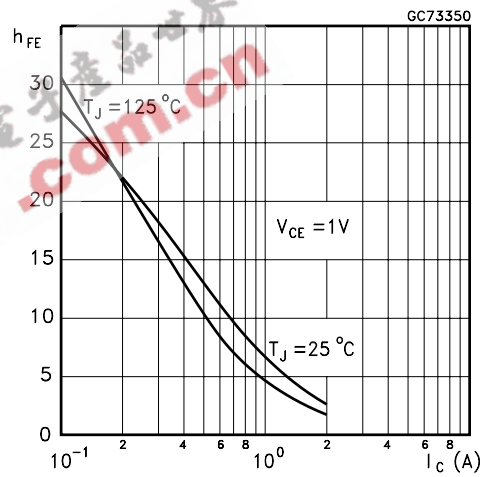
Derating Curve



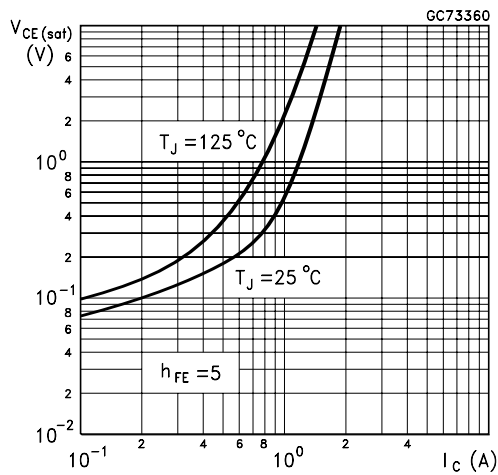
DC Current Gain



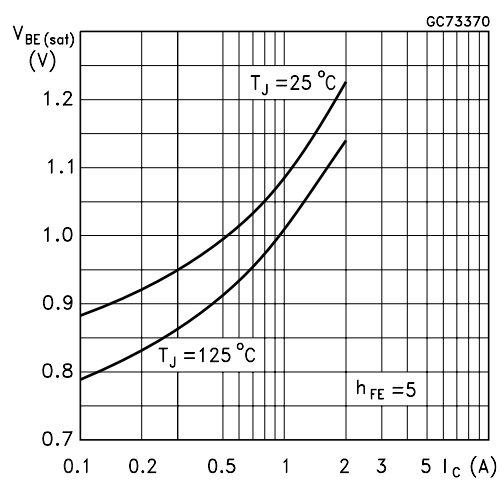
DC Current Gain



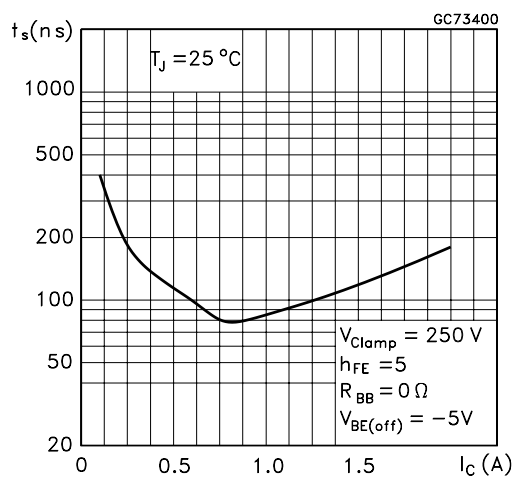
Collector Emitter Saturation Voltage



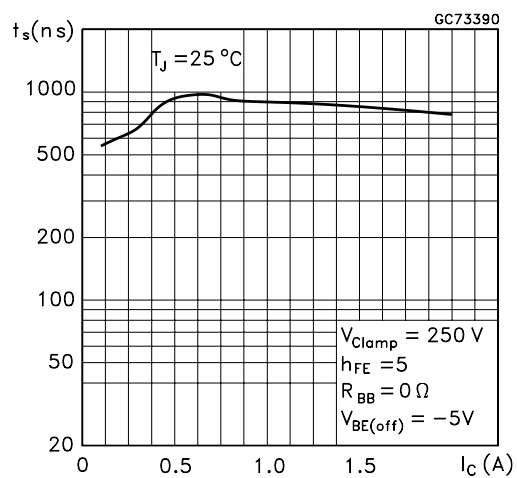
Base Emitter Saturation Voltage



Inductive Load Fall Time



Inductive Load Storage Time



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Figure 1: Inductive Load Switching Test Circuits.

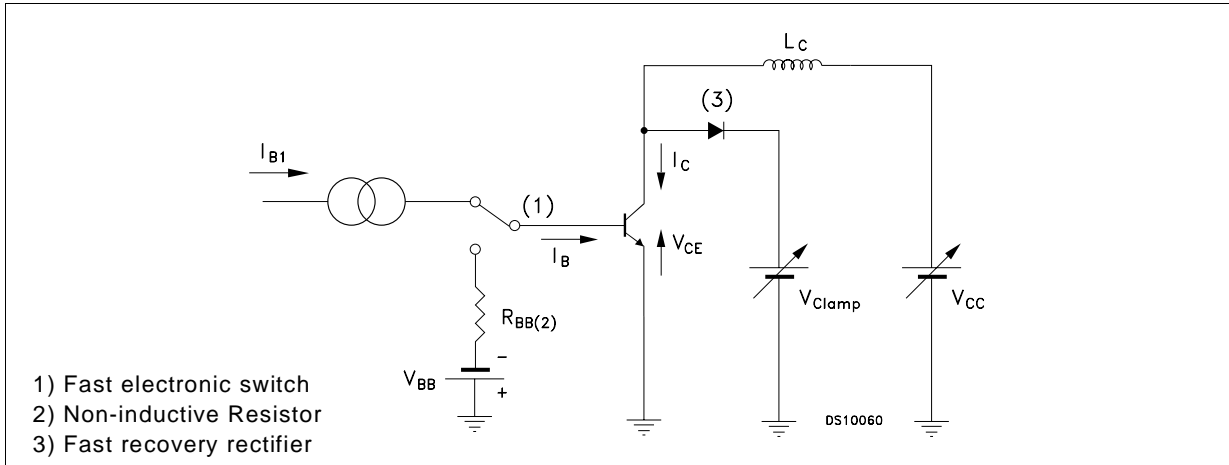
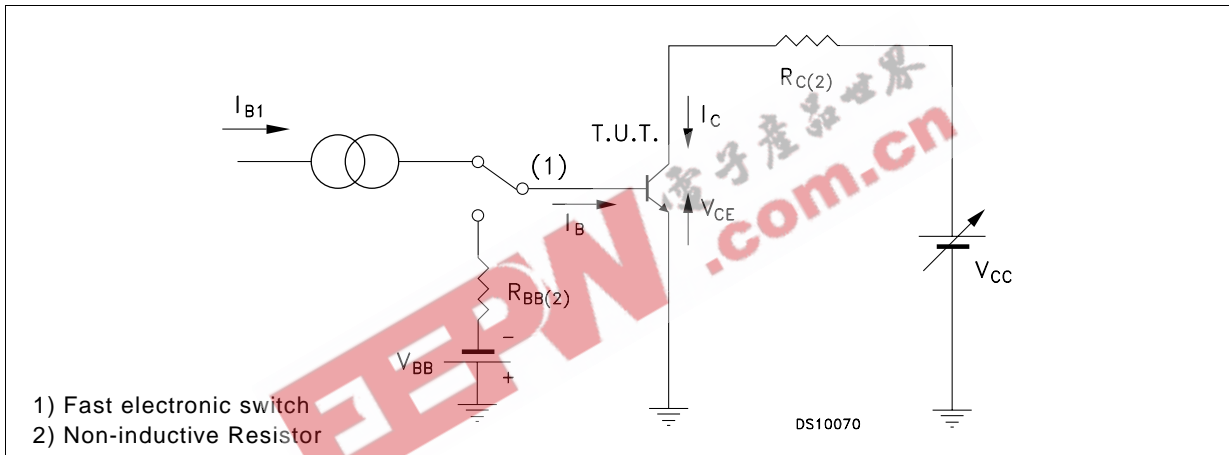
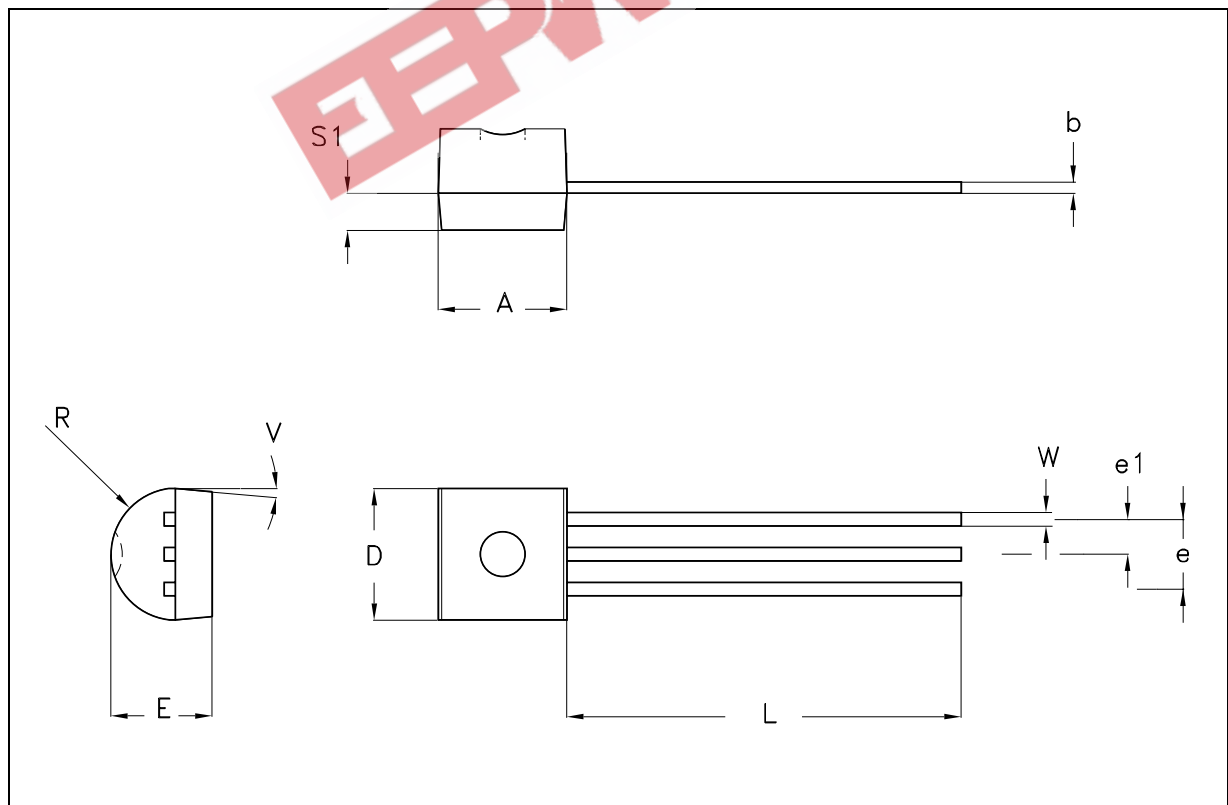


Figure 2: Resistive Load Switching Test Circuits.



TO-92 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.32		4.95	0.170		0.195
b	0.36		0.51	0.014		0.020
D	4.45		4.95	0.175		0.194
E	3.30		3.94	0.130		0.155
e	2.41		2.67	0.095		0.105
e1	1.14		1.40	0.045		0.055
L	12.70		15.49	0.500		0.609
R	2.16		2.41	0.085		0.094
S1	1.14		1.52	0.045		0.059
W	0.41		0.56	0.016		0.022
V	4 degree		6 degree	4 degree		6 degree



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